Noninverting Buffer / CMOS Logic Level Shifter with LSTTL-Compatible Inputs

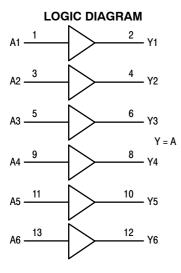
The MC74VHCT50A is a hex noninverting buffer fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

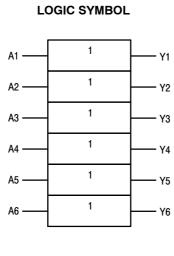
The internal circuit is composed of three stages, including a buffered output which provides high noise immunity and stable output.

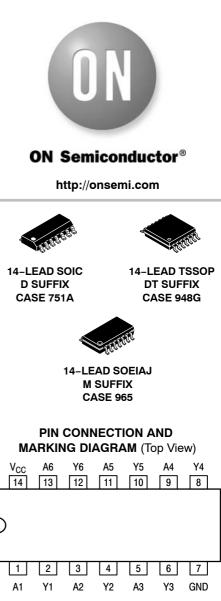
The device input is compatible with TTL-type input thresholds and the output has a full 5 V CMOS level output swing. The input protection circuitry on this device allows overvoltage tolerance on the input, allowing the device to be used as a logic-level translator from 3.0 V CMOS logic to 5.0 V CMOS Logic or from 1.8 V CMOS logic to 3.0 V CMOS Logic while operating at the high-voltage power supply.

The MC74VHCT50A input structure provides protection when voltages up to 7 V are applied, regardless of the supply voltage. This allows the MC74VHCT50A to be used to interface 5 V circuits to 3 V circuits. The output structures also provide protection when $V_{CC} = 0$ V. These input and output structures help prevent device destruction caused by supply voltage – input/output voltage mismatch, battery backup, hot insertion, etc.

- High Speed: $t_{PD} = 3.5$ ns (Typ) at $V_{CC} = 5$ V
- Low Power Dissipation: $I_{CC} = 2 \mu A$ (Max) at $T_A = 25^{\circ}C$
- TTL-Compatible Inputs: $V_{IL} = 0.8 \text{ V}$; $V_{IH} = 2.0 \text{ V}$
- CMOS–Compatible Outputs: $V_{OH} > 0.8 V_{CC}$; $V_{OL} < 0.1 V_{CC}$ @Load
- Power Down Protection Provided on Inputs and Outputs
- These Devices are Pb-Free and are RoHS Compliant







For detailed package marking information, see the Marking Diagram section on page 4 of this data sheet.

FUNCTION TABLE

A Input	Y Output
L	L
Н	Н

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

MAXIMUM RATINGS

Symbol	Parameter		Value	Unit
V _{CC}	DC Supply Voltage		-0.5 to +7.0	V
V _{IN}	DC Input Voltage		$-0.5\leqV_{ }\leq+7.0$	V
V _{OUT}	DC Output Voltage Output in HI	GH or LOW State (Note 1)	$-0.5 \le V_0 \le +7.0$	V
I _{IK}	DC Input Diode Current		-20	mA
I _{OK}	DC Output Diode Current		±20	mA
I _O	DC Output Source/Sink Current		±25	mA
I _{CC}	DC Supply Current per Supply Pin		±50	mA
I _{GND}	DC Ground Current per Ground Pin		±50	mA
T _{STG}	Storage Temperature Range		-65 to +150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds		260	°C
TJ	Junction Temperature under Bias		+ 150	°C
θ_{JA}	Thermal Resistance	SOIC TSSOP	125 170	°C/W
P _D	Power Dissipation in Still Air	SOIC TSSOP	500 450	mW
V _{ESD}	-	iman Body Model (Note 2) Machine Model (Note 3) ged Device Model (Note 4)	> 2000 > 200 2000	V
I _{Latch-Up}	$\label{eq:latch-Up} \mbox{Performance} \qquad \mbox{Above V}_{CC} \mbox{ and Be}$	low GND at 85°C (Note 5)	±300	mA

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

I_O absolute maximum rating must be observed.
 Tested to EIA/JESD22-A114-A.

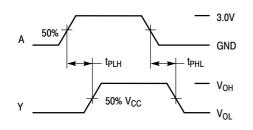
3. Tested to EIA/JESD22-A115-A.

4. Tested to JESD22-C101-A.

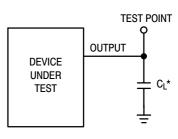
5. Tested to EIA/JESD78.

RECOMMENDED OPERATING CONDITIONS

Characteristics	Symbol	Min	Max	Unit
DC Supply Voltage	V _{CC}	2.0	5.5	V
DC Input Voltage	V _{IN}	0.0	5.5	V
DC Output Voltage V _{CC} = 0 High or Low State	V _{OUT}	0.0 0.0	5.5 V _{CC}	V
Operating Temperature Range	T _A	-55	+125	°C
Input Rise and Fall Time $\begin{array}{ll} V_{CC} = 3.3 \ V \pm 0.3 \ V \\ V_{CC} = 5.0 \ V \pm 0.5 \ V \end{array}$	t _r , t _f	0 0	100 20	ns/V







*Includes all probe and jig capacitance

Figure 2. Test Circuit

			Vcc	ר	r _A = 25°0	2	TA ≤	85°C	TA ≤ ⁻	125°C	
Symbol	Parameter	Test Conditions	(V)	Min	Тур	Max	Min	Max	Min	Max	Unit
V _{IH}	Minimum High-Level Input Voltage		3.0 4.5 5.5	1.2 2.0 2.0			1.2 2.0 2.0		1.2 2.0 2.0		V
V _{IL}	Maximum Low-Level Input Voltage		3.0 4.5 5.5			0.53 0.8 0.8		0.53 0.8 0.8		0.53 0.8 0.8	V
V _{OH}	Minimum High-Level Output Voltage	V _{IN} = V _{IH} or V _{IL} I _{OH} = -50 μA	3.0 4.5	2.9 4.4	3.0 4.5		2.9 4.4		2.9 4.4		V
	$V_{IN} = V_{IH} \text{ or } V_{IL}$		3.0 4.5	2.58 3.94			2.48 3.80		2.34 3.66		V
V _{OL}	Maximum Low-Level Output Voltage	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 50 \ \mu\text{A}$	3.0 4.5		0.0 0.0	0.1 0.1		0.1 0.1		0.1 0.1	V
	$V_{IN} = V_{IH} \text{ or } V_{IL}$		3.0 4.5			0.36 0.36		0.44 0.44		0.52 0.52	V
I _{IN}	Maximum Input Leakage Current	V _{IN} = 5.5 V or GND	0 to 5.5			±0.1		±1.0		±1.0	μA
I _{CC}	Maximum Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND	5.5			2.0		20		40	μA
I _{CCT}	Quiescent Supply Current	Input: V _{IN} = 3.4 V	5.5			1.35		1.50		1.65	mA
I _{OFF}	Output Leakage Current	V _{OUT} = 5.5 V	0.0			0.5		5.0		10	μA

DC ELECTRICAL CHARACTERISTICS

AC ELECTRICAL CHARACTERISTICS ($C_{load} = 50 \text{ pF}$, Input $t_r = t_f = 3.0 \text{ns}$)

				T _A = 25°C		2	T_A ≤ 85°C		T _A ≤ 125°C		
Symbol	Parameter	Test Condi	tions	Min	Тур	Max	Min	Max	Min	Max	Unit
t _{PLH} , t _{PHL}	Maximum Propogation Delay,	$V_{CC}=3.3\pm0.3~V$	C _L = 15 pF C _L = 50 pF		5.5 8.0	7.9 11.4	1.0 1.0	9.5 13.0			ns
	Input A to Y	$V_{CC} = 5.0 \pm 0.5 \text{ V}$	C _L = 15 pF C _L = 50 pF		6.2 7.0	7.5 8.5		8.5 9.5		9.5 10.5	
C _{IN}	Maximum Input Capacitance				5	10		10		10	pF
	Typical @ 25°C, V _{CC} = 5.0 V					v					

C_{PD} Power Dissipation Capacitance (Note 6) 15

6. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC}$. C_{PD} is used to determine the no-load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.

рF

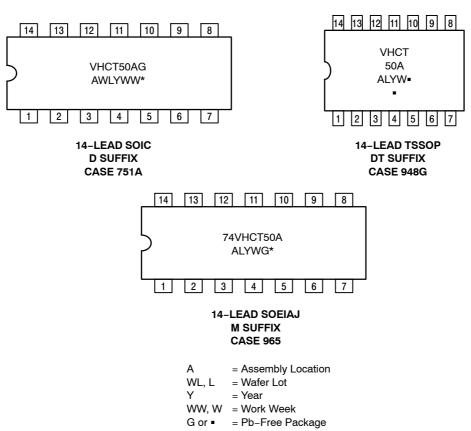
		T _A = 25°C		
Symbol	Characteristic	Тур	Max	Unit
V _{OLP}	Quiet Output Maximum Dynamic V _{OL}	0.8	1.0	V
V _{OLV}	Quiet Output Minimum Dynamic V _{OL}	-0.8	-1.0	V
V _{IHD}	Minimum High Level Dynamic Input Voltage		2.0	V
V _{ILD}	Maximum Low Level Dynamic Input Voltage		0.8	V

NOISE CHARACTERISTICS (Input $t_r = t_f = 3.0ns$, $C_L = 50pF$, $V_{CC} = 5.0V$)

ORDERING INFORMATION

Device	Package	Shipping [†]
MC74VHCT50ADG	SOIC-14 (Pb-Free)	55 Units / Rail
MC74VHCT50ADR2G	SOIC-14 (Pb-Free)	2500 / Tape & Reel
MC74VHCT50ADTG	TSSOP-14 (Pb-Free)	96 Units / Rail
MC74VHCT50ADTR2G	TSSOP-14 (Pb-Free)	2500 / Tape & Reel
MC74VHCT50AMG	SOEIAJ (Pb-Free)	50 Units / Rail
MC74VHCT50AMELG	SOEIAJ (Pb-Free)	2000 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



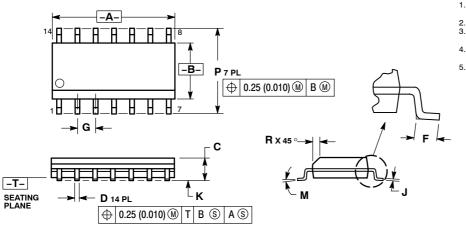
MARKING DIAGRAMS

(Top View)

*See Applications Note #AND8004/D for date code and traceability information.

PACKAGE DIMENSIONS

SOIC-14 **D SUFFIX** CASE 751A-03 **ISSUE J**

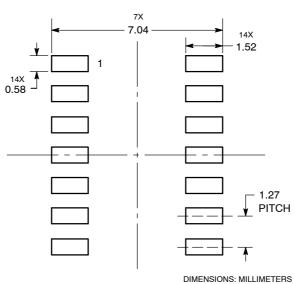


- NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETER. 3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION. 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE. 5. DIMENSION D DOES NOT INCLUDE

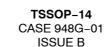
PER SIDE. 5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION CONDITION.

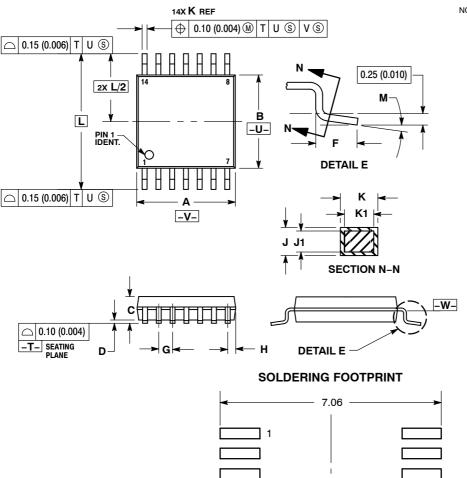
	MILLIN	IETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	8.55	8.75	0.337	0.344	
В	3.80	4.00	0.150	0.157	
С	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.27	BSC	0.050 BSC		
J	0.19	0.25	0.008	0.009	
К	0.10	0.25	0.004	0.009	
М	0 °	7 °	0 °	7 °	
Ρ	5.80	6.20	0.228	0.244	
R	0.25	0.50	0.010	0.019	

SOLDERING FOOTPRINT



PACKAGE DIMENSIONS



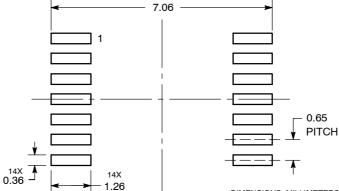


- NOTES: 1. DIMENSIONING AND TOLERANCING PER
 - DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
 DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.
 MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
 DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION.
 INTERLEAD FLASH OR PROTRUSION.
 INTERLEAD FLASH OR PROTRUSION.
 INTERLEAD FLASH OR PROTRUSION.
 DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K

 - (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL

DIMENSION AT MAXIMUM MALEHIAL CONDITION. 6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY. 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

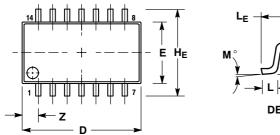
	MILLIN	IETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	4.90	5.10	0.193	0.200	
В	4.30	4.50	0.169	0.177	
С		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	BSC	0.026 BSC		
Н	0.50	0.60	0.020	0.024	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
к	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40 BSC		0.252 BSC		
м	0 °	8 °	0 °	8 °	

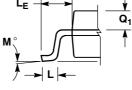


DIMENSIONS: MILLIMETERS

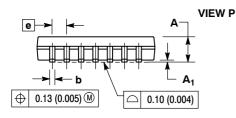
PACKAGE DIMENSIONS

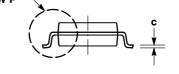
SOEIAJ-14 CASE 965-01 ISSUE B





DETAIL P





NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

2. CONTROLLING DIMENSION: MILLIMETER. 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH

MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE. TERMINAL NUMBERS ARE SHOWN FOR

4. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.

THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α		2.05		0.081
A ₁	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
C	0.10	0.20	0.004	0.008
D	9.90	10.50	0.390	0.413
Е	5.10	5.45	0.201	0.215
е	1.27 BSC		0.050) BSC
HE	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
LE	1.10	1.50	0.043	0.059
Μ	0 °	10 °	0 °	10 °
Q ₁	0.70	0.90	0.028	0.035
Z		1.42		0.056

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